

isc Silicon NPN Power Transistor

2SC4793

DESCRIPTION

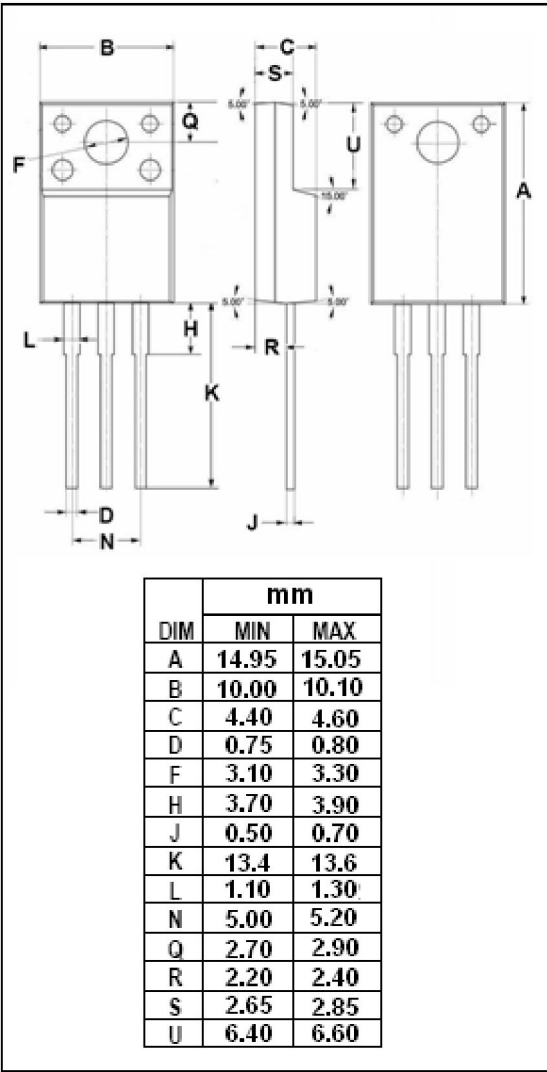
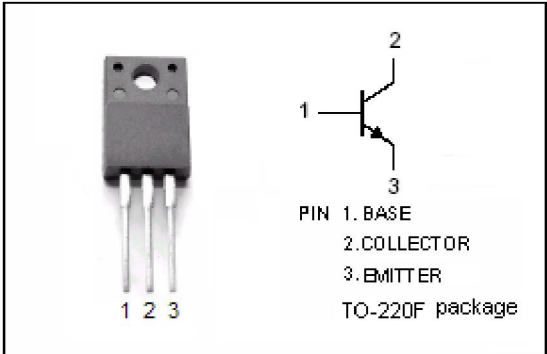
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 230V(\text{Min})$
- High Current-Gain Bandwidth Product
- Complement to Type 2SA1837

APPLICATIONS

- Power amplifier applications.
- Driver stage amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	230	V
V_{CEO}	Collector-Emitter Voltage	230	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	1	A
I_B	Base Current-Continuous	0.1	A
P_C	Collector Power Dissipation @ $T_a=25^{\circ}\text{C}$	2	W
	Collector Power Dissipation @ $T_c=25^{\circ}\text{C}$	20	
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~150	$^{\circ}\text{C}$



isc Silicon NPN Power Transistor**2SC4793****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA ; I _B = 0	230			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 500mA; I _B = 50mA			1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 500mA ; V _{CE} = 5V			1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 230V ; I _E =0			1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C =0			1.0	μ A
h _{FE}	DC Current Gain	I _C = 100mA; V _{CE} = 5V	100		320	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f= 1MHz		20		pF
f _T	Current-Gain—Bandwidth Product	I _C = 100mA ; V _{CE} = 10V		100		MHz